Scalable GaInP/GaAs HBT large-signal model (2000 Vol. II [MWSYM])

M. Rudolph, R. Doerner, K. Beilenhoff and P. Heymann. "Scalable GaInP/GaAs HBT large-signal model (2000 Vol. II [MWSYM])." 2000 MTT-S International Microwave Symposium Digest 00.2 (2000 Vol. II [MWSYM]): 753-756.

A scalable large-signal model for heterojunction bipolar transistors (HBTs) is presented. It allows exact modeling of all transistor parameters from single finger elementary cells to multifinger power devices. The scaling rules are given in detail. The model is verified by comparison with measurements of GaInP/GaAs-HBTs.

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